

# Transistores bipolares:

## Construção, caraterísticas e aplicações

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# Descrição simples do transistor - Bipolar junction transistor [BOYLESTAD]

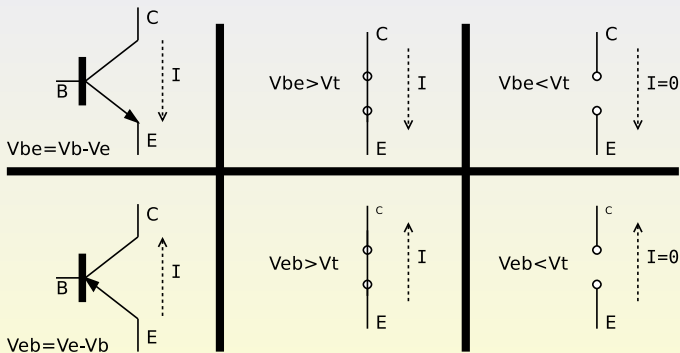


Figure : Descrição do BJT em saturação

# Semicondutor

$$R = \frac{\rho l}{A}$$

$\rho$ : ohmios-metro

QUADRO 1.1 Valores de Resistividade Típicos

<i>Condutor</i>	<i>Semicondutor</i>	<i>Isolante</i>
$\rho \cong 10^{-6} \Omega\text{-cm}$ (cobre)	$\rho \cong 50 \Omega\text{-cm}$ (germânio) $\rho \cong 50 \times 10^3 \Omega\text{-cm}$ (silício)	$\rho \cong 10^{12} \Omega\text{-cm}$ (mica)

Conductor < semicondutor < Isolante

Figure : Resistência ao fluxo de carga

# Materiais condutores

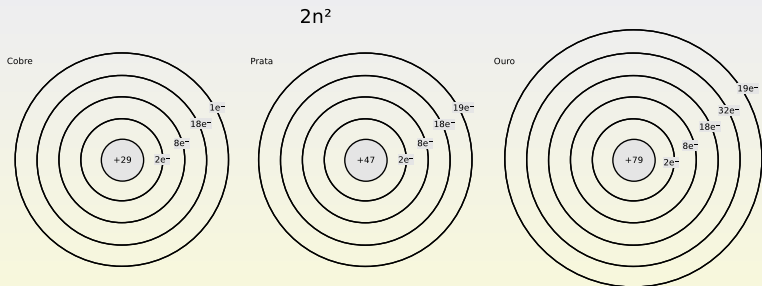


Figure : Elétrons nas camadas e camadas de valência

# Materiais semicondutores

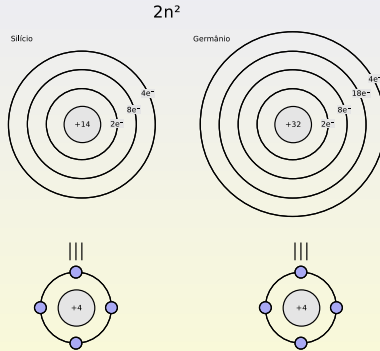


Figure : Elétrons nas camadas e camadas de valência

# Semicondutor intrínseco

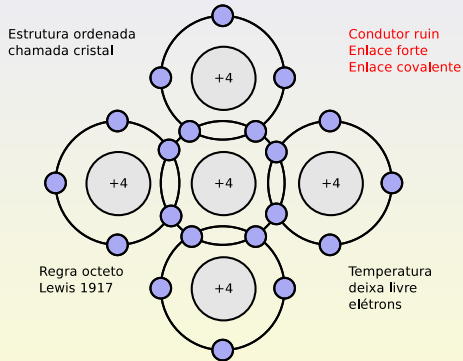
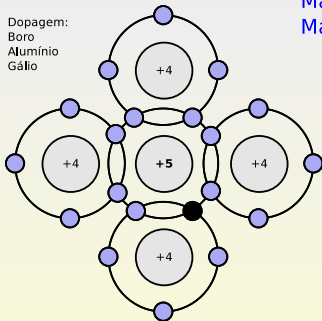


Figure : Semicondutor intrínseco (Semicondutor Puro)

# Dopagem: Semicondutor extrínseco tipo P



Maior quantidade de buracos  
Maior condutividade

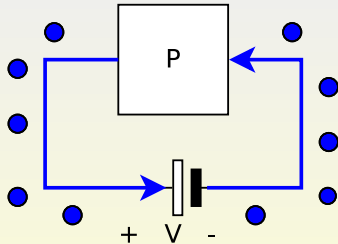
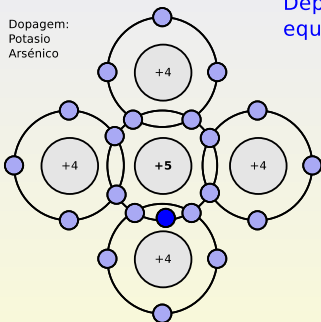


Figure : Semicondutor extrínseco tipo P

# Dopagem: Semicondutor extrínseco tipo N



Depois de uma transição é  
equivalente a um semicondutor puro

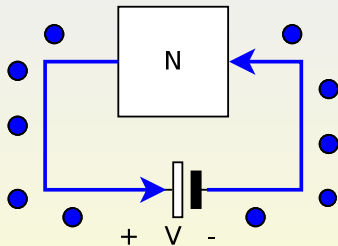


Figure : Semicondutor extrínseco tipo N



# União PN

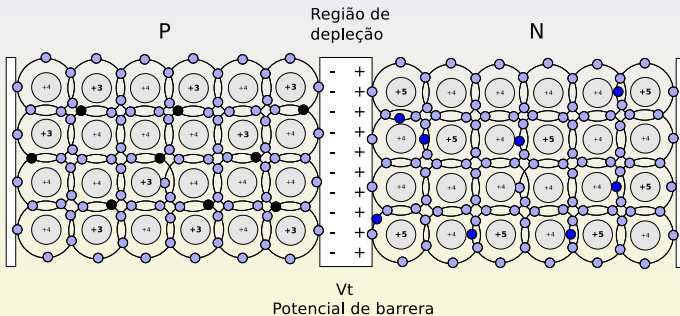


Figure : União PN

# União PN - Polarização direta

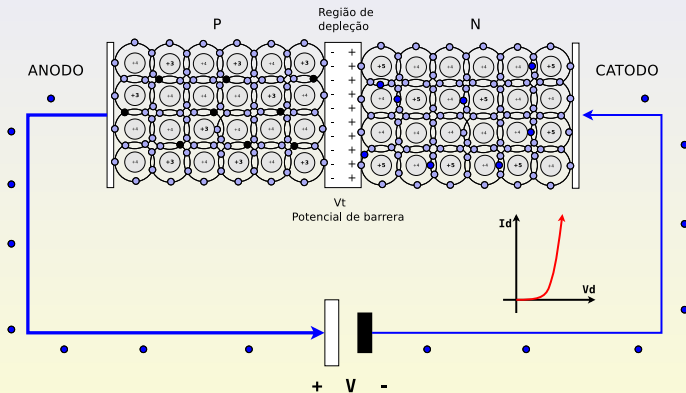


Figure : Polarização direta

# União PN - Polarização inversa

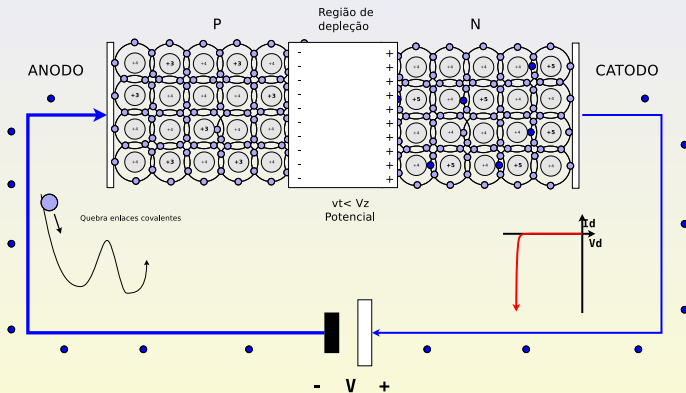


Figure : Polarização inversa

# União NPN e PNP

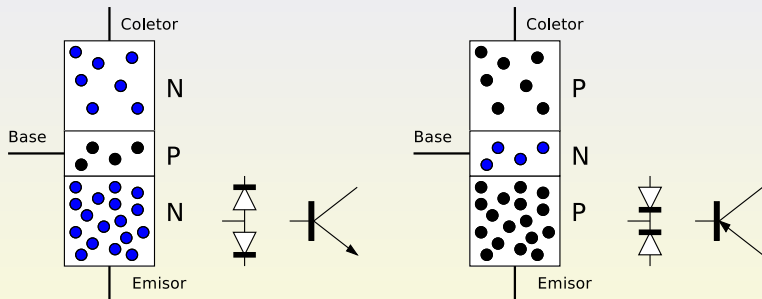


Figure : Transistor BJT - Sem polarização

# Transistor NPN polarizado

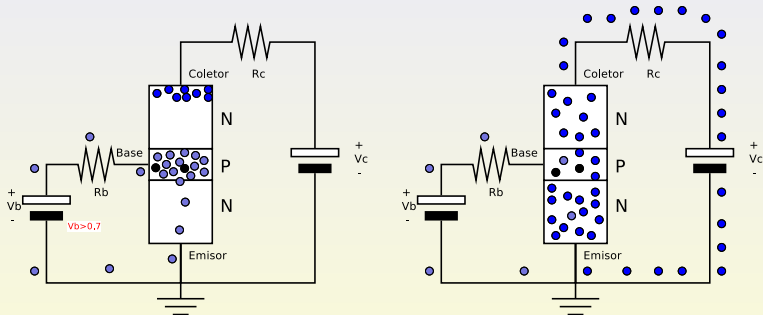
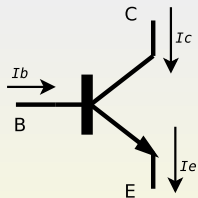


Figure : Transistor BJT

# Ganho de corrente num BJT em DC



$$I_b + I_c = I_e$$

$$h_{fe} \equiv \beta_{dc} = \frac{I_c}{I_b}$$

$$\alpha_{dc} = \frac{I_c}{I_e}$$

20 < hfe < 100 Potencia

100 < hfe < 300 sinal

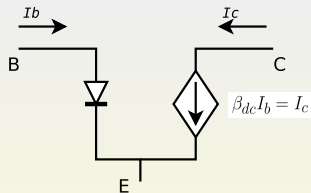
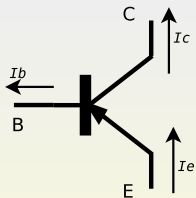


Figure : NPN - Ganho de corrente

# Ganho de corrente num BJT em DC



$$I_b + I_c = I_e$$

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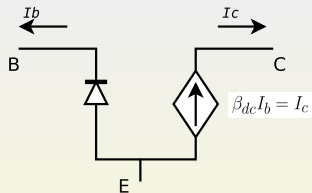


Figure : PNP - Ganho de corrente

# Curva do transistor

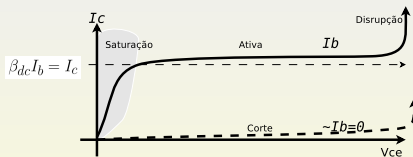
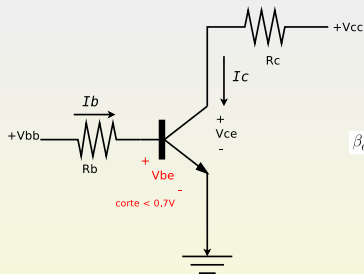


Figure : Curva característica do transistor



# Corte e saturação

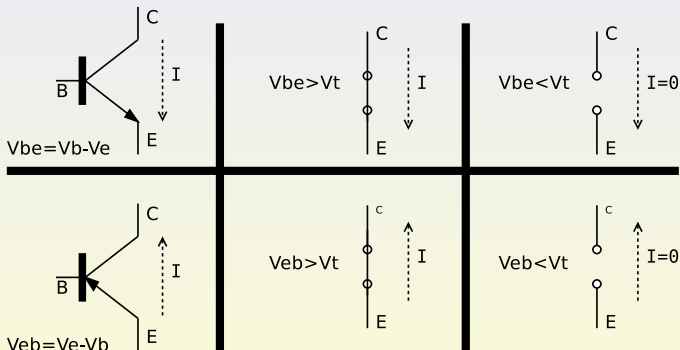


Figure : Descrição do BJT em saturação e corte

# Levar um transistor na região de corte

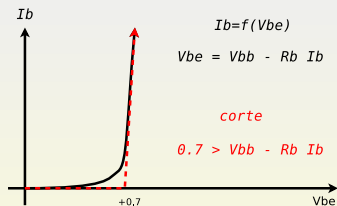
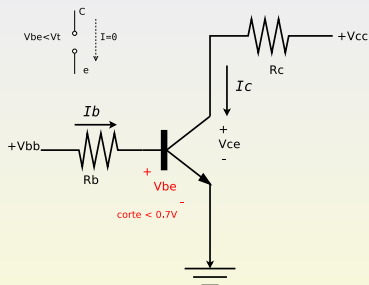


Figure : Transistor em corte

# Levar um transistor na região de ativa

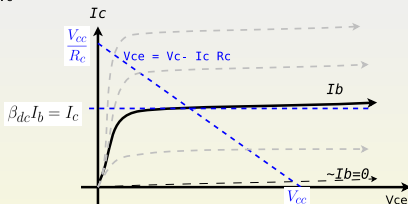
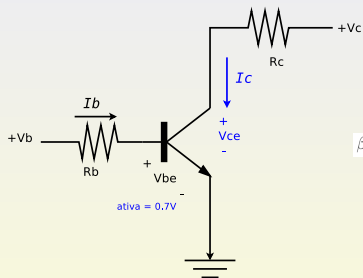


Figure : Transistor na região ativa

# Levar um transistor na região de saturação

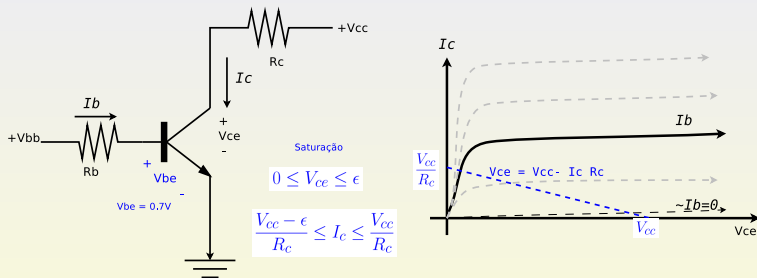


Figure : Transistor na região de saturação

## Exemplo de cálculo de valores de resistência

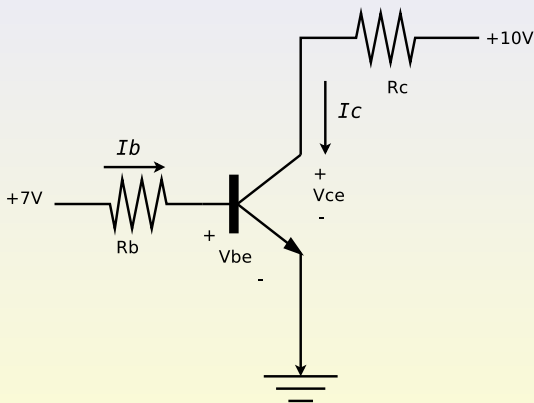


Figure : Levar o transistor na região de corte

# Circuitos uteis

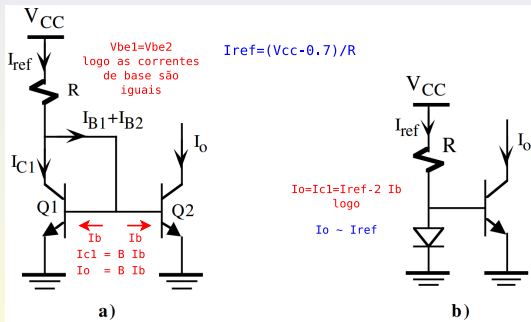


Figure : Espelho de corrente

# References I

[BOYLESTAD] BOYLESTAD, R. *DISPOSITIVOS  
ELETRONICOS E TEORIA DE CIRCUITOS*. LTC.